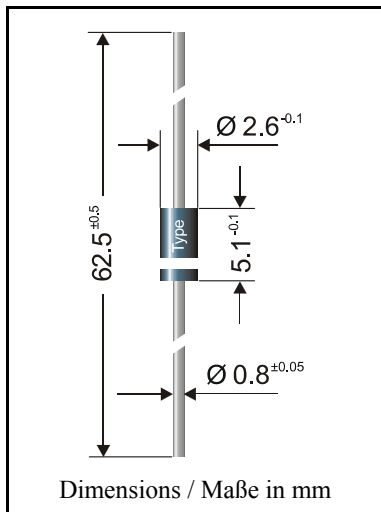


**Bidirectional Si-Trigger-Diodes (DIAC)**

**Bidirektionale Si-Trigger-Dioden (DIAC)**



|                                              |                |
|----------------------------------------------|----------------|
| Breakdown voltage                            | 28 ... 45 V    |
| Durchbruchsspannung                          |                |
| Peak pulse current – Max. Triggerimpuls      | ± 2 A          |
| Plastic case                                 | DO-41          |
| Kunststoffgehäuse                            | DO-204AL       |
| Plastic material has UL classification 94V-0 |                |
| Gehäusematerial UL94V-0 klassifiziert        |                |
| Weight approx. – Gewicht ca.                 | 0.13 g         |
| Standard packaging taped in ammo pack        | see page 16    |
| Standard Lieferform gegurtet in Ammo-Pack    | siehe Seite 16 |

**Maximum ratings**

**Grenzwerte**

|                                                         |                                    |                  |                      |
|---------------------------------------------------------|------------------------------------|------------------|----------------------|
| Power dissipation – Verlustleistung                     | $T_A = 50\text{ }^{\circ}\text{C}$ | $P_{\text{tot}}$ | 150 mW <sup>1)</sup> |
| Peak pulse current (120 pulse repetition rate)          | $t_p \leq 10\text{ }\mu\text{s}$   | $I_{\text{PM}}$  | ± 2 A <sup>1)</sup>  |
| Max. Triggerstrom (120 Impulse)                         |                                    |                  |                      |
| Operating junction temperature – Sperrschichttemperatur |                                    | $T_j$            | – 40...+100°C        |
| Storage temperature – Lagerungstemperatur               |                                    | $T_s$            | – 40...+150°C        |

**Characteristics**

**Kennwerte**

|                                                                 |                                                       |                  |                         |                          |
|-----------------------------------------------------------------|-------------------------------------------------------|------------------|-------------------------|--------------------------|
| Breakdown voltage                                               | $dV/dt = 10\text{ V}/\mu\text{s}$                     | BR 100/03 DO-41  | $V_{\text{BO}}$         | 28 ... 36 V              |
| Durchbruchsspannung                                             |                                                       | BR 100/031 DO-41 | $V_{\text{BO}}$         | 30 ... 34 V              |
|                                                                 |                                                       | BR 100/04 DO-41  | $V_{\text{BO}}$         | 35 ... 45 V              |
| Breakdown current – Durchbruchstrom                             | $V = 98\text{ \% } V_{\text{BO}}$                     |                  | $I_{\text{BO}}$         | < 50 $\mu\text{A}$       |
| Asymmetry of breakdown voltage                                  | $ V_{(\text{BO})\text{F}} - V_{(\text{BO})\text{R}} $ |                  | $\Delta V_{\text{BO}}$  | < 3.8 V                  |
| Unsymmetrie der Durchbruchspannung                              |                                                       |                  |                         |                          |
| Foldback voltage – Spannungs-Rücksprung                         | $dV/dt = 10\text{ V}/\mu\text{s}$                     |                  | $\Delta V_{\text{F/R}}$ | > 5 V                    |
| $\Delta I = I_{\text{BR}}$ to/auf $I_{\text{F}} = 10\text{ mA}$ |                                                       |                  |                         |                          |
| Thermal resistance junction to ambient air                      |                                                       |                  | $R_{\text{thA}}$        | < 0.3 K/mW <sup>1)</sup> |
| Wärmewiderstand Sperrschicht – umgebende Luft                   |                                                       |                  |                         |                          |

<sup>1)</sup> Valid, if leads are kept at ambient temperature at a distance of 10 mm from case

Gültig, wenn die Anschlußdrähte in 10 mm Abstand vom Gehäuse auf Umgebungstemperatur gehalten werden

